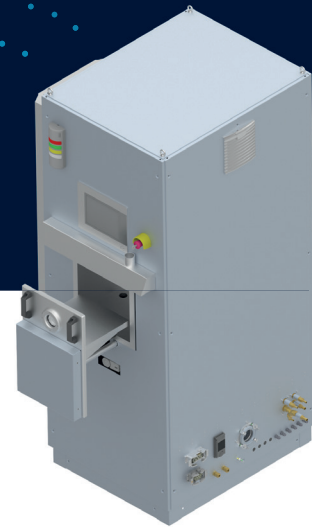


MICROWAVE PLASMA SYSTEM MA3000D-561BB

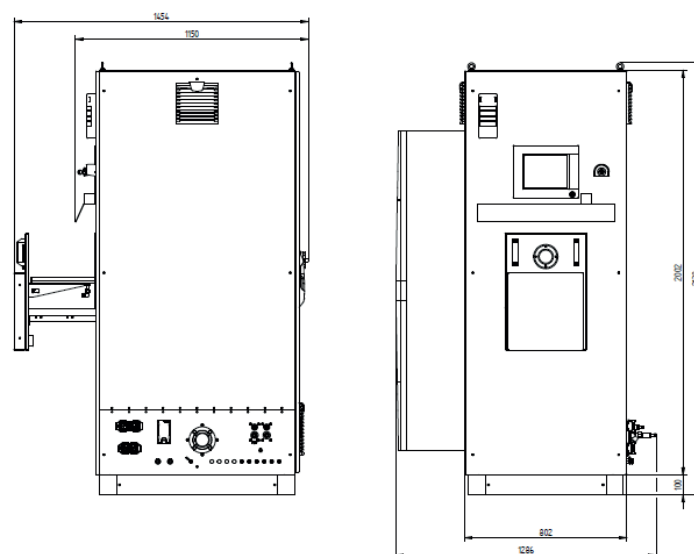
PLASMA DECAPSULATION TOOL (3 KW / 2450 MHZ)



Features

- Optimised for decapsulation of microchips
- Short decapsulation time without damage of critical areas by ion bombardment
- Very high etch rate: > 0.2 mm per hour including anorganic filling materials
- No attack of materials such as Au, Al, Cu and Pd
- No attack of wiring (e.g. Cu and Pd-Cu materials)
- Selectivity > 500 : 1
- Decapsulation time: 1 - 3 hours typically after laser ablation
- Integrated, highly efficient microwave plasma source
- Fast, isotropic etching by radicals only
- No ions, no MW radiation and no electrical fields in the area of the samples
- Suitable for substrate sizes up to 300 mm

Outline Dimensions (mm)



Specifications

Mains voltage	3~ (L1 / L2 / L3 / PE) 400 V, 35,07 A, 50 Hz
Mains leakage current	3,5 mA @ 440/520 VAC/50 Hz
Cooling	Air / Water ≥ 10 (2,64) l/min (US.gal/min) 4 - 6 (58,02 - 87,02) bar (psi) @ 20 - 25 (68 - 77) °C (°F)
HF output power	3000 W
Process gases	O ₂ , N ₂ , CF ₄ , SF ₆ , N ₂ H ₂
Vacuum connection	ISO-K63

Dimensions	Width: 1286 (50,63) mm (inch) Height: 2138 (84,17) mm (inch) Depth: 1150 (45,28) mm (inch)
Size of working plate	320 x 320 (12.60 x 12.60) mm (inch)
Weight	480 (1058,22) kg (lbs)
Conditions	In operation: 5 °C (41 °F) - 40 °C (104 °F), relative humidity 80 % to 30 °C (86 °F), above this linearly reduced to 50 %, non-condensing, 3K3 Storage: - 25 °C (-13 °F) - + 70 °C (158 °F), 70 kPa - 106 kPa, relative humidity 80 % to 30 °C (86 °F), above this linearly reduced to 50 %, non-condensing, 1K3
Frequency	2450 MHz
Compressed air	6 - 9 (87,02 - 130,53) bar (psi) Oil free, dry, 5 µm filtered

Recommended system components

- Vacuum pump (dry pump min. 300 m³/h, recommended 600 m³/h)
- Gas cleaning system (CS CLEAN dry absorber)